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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/801,219
				Filing Date	3/16/2004
				First Named Inventor	David J. Megaw
				Art Unit	N/A
				Examiner Name	National Semiconductor
				Attorney Docket Number	08211/0200387-US0/P05824
Sheet	1	of	1		

3 U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
JA	AA	US-6,342,781	01/29/02	Laraia	
JA	AB	US-4,808,908	02/28/1989	Lewis et al.	
JA	AC	US-4,443,753	04/17/1984	McGlinchey	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				

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6 NON PATENT LITERATURE DOCUMENTS						
Examiner Initials [*]	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T ²
JA	CA	AUDY, JONATHAN M. 3 rd order curvature corrected Bandgap Cell. IEEE, 1996, 397-400. (no month)				
JA	CB	AZARKAN, AHMIDOU, ARIE VAN STAVEREN and FABIANO FRUETT. A Low-noise Bandgap Reference Voltage Source with Curvature Correction. IEEE, 2002, 205-208. (no month)				
JA	CC	GUNAWAN, MADE ET AL. A Curvature-Corrected Low-Voltage Bandgap Reference. IEEE, 1993, 667670. (no month)				
JA	CD	GUPTA, SANDHYA and WILLIAM BLACK. A 3 to 5V CMOS Bandgap Voltage Reference with Novel Trimming. IEEE, 1997, 969-972. (no month)				
JA	CE	LEUNG, KA NANG, PHILIP K.T. MOK and CHI YAT LEUNG. A 2-V 23- μ A 5.3-ppm/ $^{\circ}$ C 4 th Order Curvature-Compensated CMOS Bandgap Reference. IEEE Custom Integrated Circuits Conference, 2002, 457-460. (no month)				
JA	CF	MICHEJDA, JOHN and SUK K. KIM. A Precision CMOS Bandgap Reference. IEEE Journal of Solid-State Circuits, December 1984, Vol. Sc 19:6: 1014-1021..				

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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(S:1821 1102003)	J. Han	Date Considered	1/6/06
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